

## SWITCHING REGULATOR APPLICATIONS

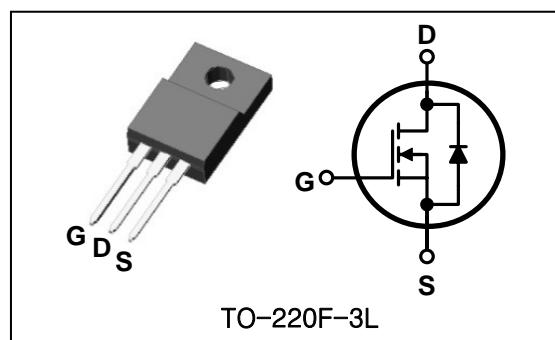
### Features

- High Voltage :  $BV_{DSS}=200V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=55pF$ (Typ.)
- Low gate charge :  $Q_g=22nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.17\Omega$ (Max.)

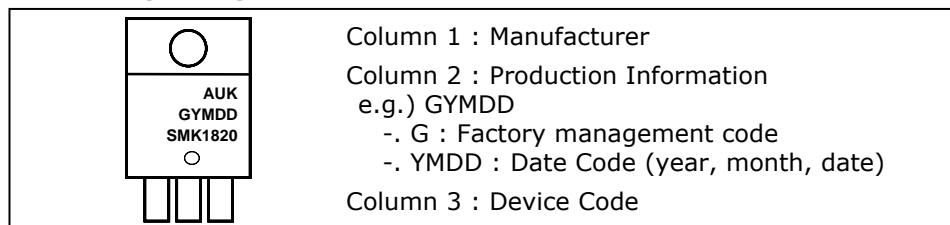
### Ordering Information

Type No.	Marking	Package Code
SMK1820F	SMK1820	TO-220F-3L

### PIN Connection



### Marking Diagram



### Absolute maximum ratings ( $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	200	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current (DC) *	$I_D$	$T_c=25^\circ C$	A
		$T_c=100^\circ C$	A
Drain current (Pulsed) *	$I_{DM}$	72	A
Power dissipation	$P_D$	35	W
Avalanche current (Single) ②	$I_{AS}$	18	A
Single pulsed avalanche energy ②	$E_{AS}$	453.	mJ
Avalanche current (Repetitive) ①	$I_{AR}$	18	A
Repetitive avalanche energy ①	$E_{AR}$	13.9	mJ
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55~150	

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-C)}$	-	3.57	$^\circ C/W$
	$R_{th(J-A)}$	-	62.5	

## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	200	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	$I_{\text{DSS}}$	$V_{DS}=200\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{\text{GSS}}$	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance ④	$R_{DS(\text{on})}$	$V_{GS}=10\text{V}, I_D=9.0\text{A}$	-	0.14	0.17	$\Omega$
Forward transfer conductance ④	$g_{fs}$	$V_{DS}=10\text{V}, I_D=9.0\text{A}$	-	10.5	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1 \text{ MHz}$	-	942	1240	pF
Output capacitance	$C_{oss}$		-	227	310	
Reverse transfer capacitance	$C_{rss}$		-	55	71	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=125\text{V}, I_D=18\text{A}$ $R_G=25\Omega$	-	15	-	ns
Rise time	$t_r$		-	130	-	
Turn-off delay time	$t_{d(\text{off})}$		-	135	-	
Fall time	$t_f$		-	105	-	
Total gate charge	$Q_g$	$V_{DS}=160\text{V}, V_{GS}=10\text{V}$ $I_D=18\text{A}$	-	22	28	nC
Gate-source charge	$Q_{gs}$		-	6.6	-	
Gate-drain charge	$Q_{gd}$		-	7.2	-	

## Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

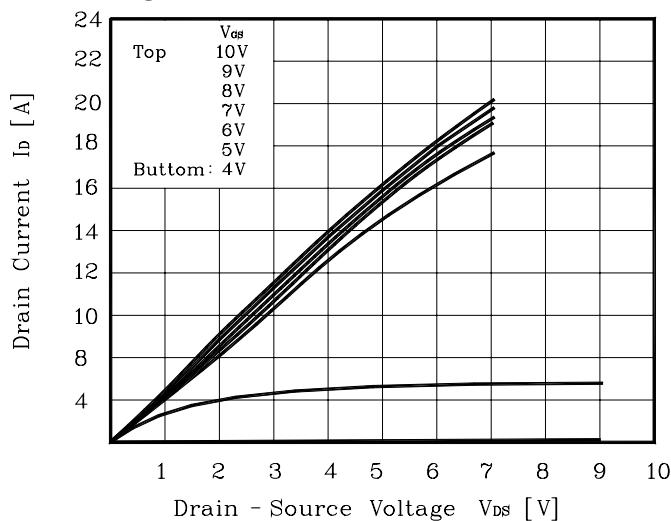
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	18	A
Source current (Pulsed) ①	$I_{SM}$		-	-	72	
Forward voltage ④	$V_{SD}$	$V_{GS}=0\text{V}, I_S=18\text{A}$	-	-	1.4	V
Reverse recovery time	$t_{rr}$	$I_S=18\text{A}, V_{GS}=0\text{V}$ $dI_F/dt=100\text{A}/\mu\text{s}$	-	208	-	ns
Reverse recovery charge	$Q_{rr}$		-	1.63	-	$\mu\text{C}$

Note :

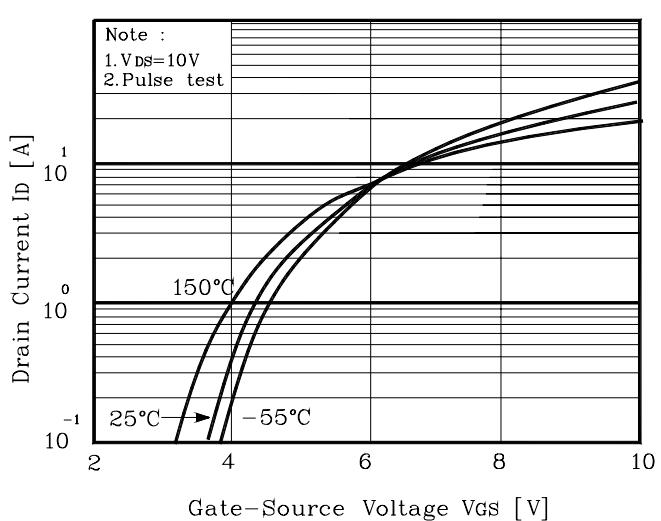
- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ②  $L=2.1\text{mH}, I_{AS}=18\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

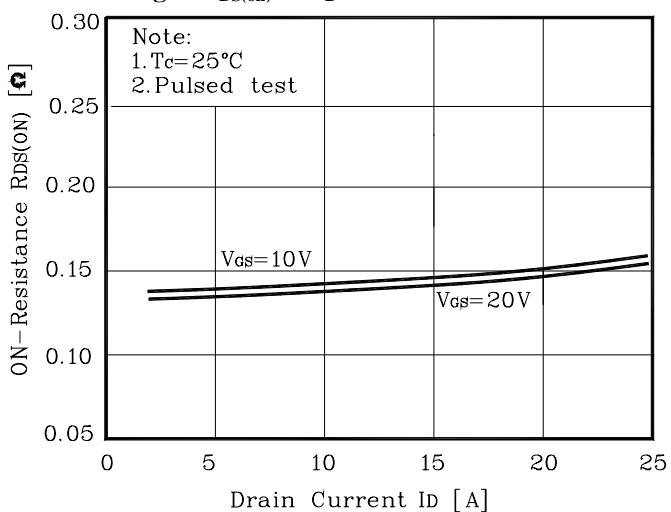
**Fig. 1  $I_D$  -  $V_{DS}$**



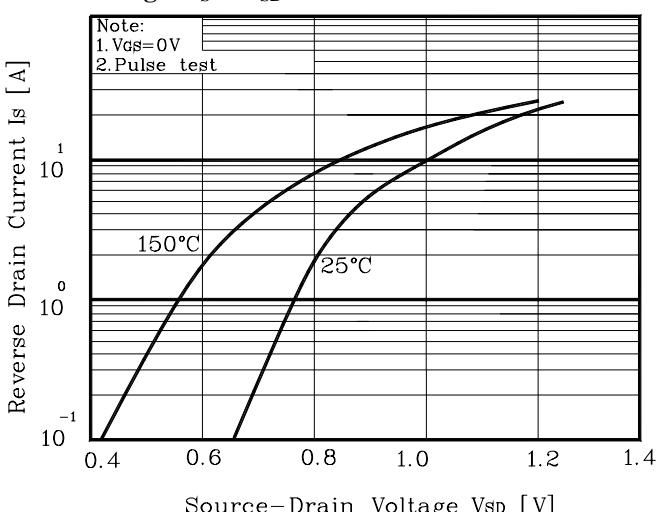
**Fig. 2  $I_D$  -  $V_{GS}$**



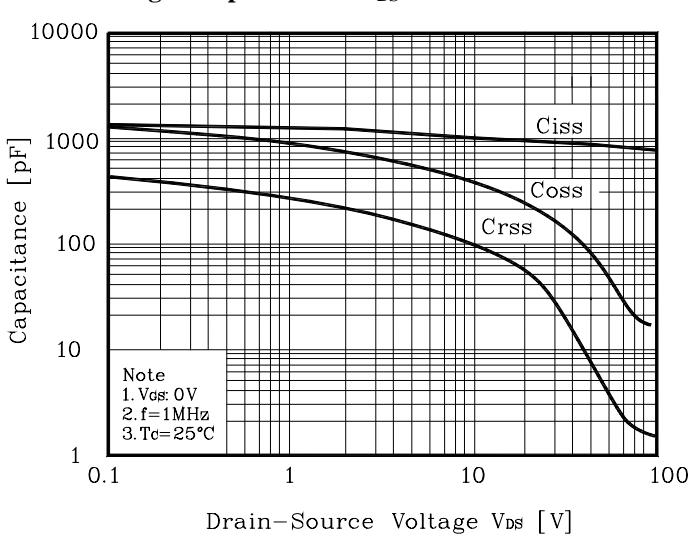
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



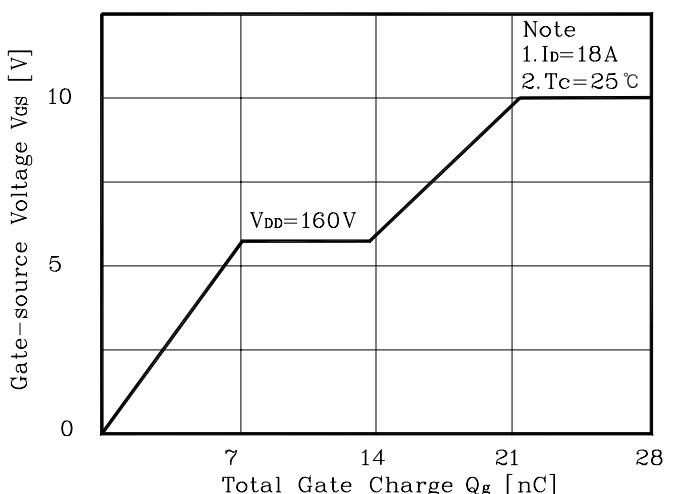
**Fig. 4  $I_S$  -  $V_{SD}$**



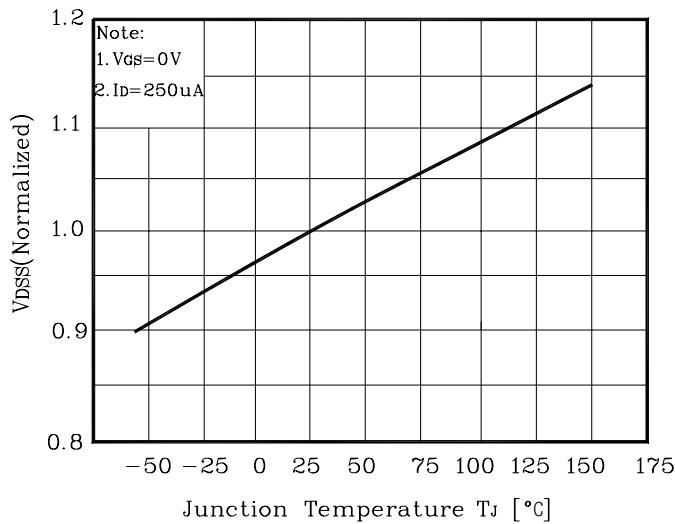
**Fig. 5 Capacitance -  $V_{DS}$**



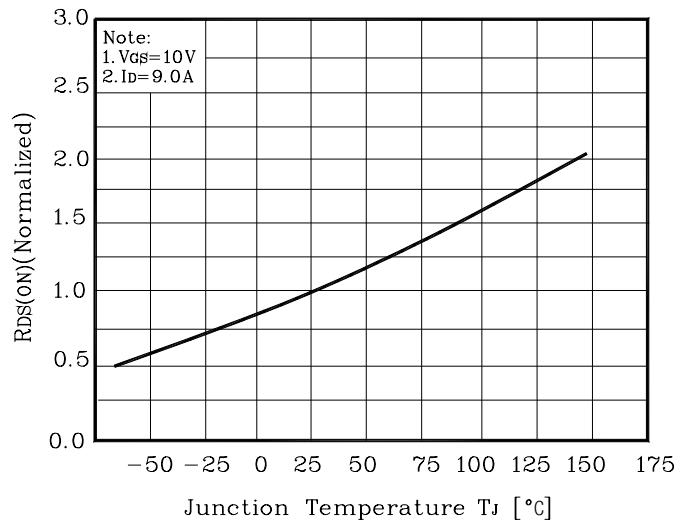
**Fig. 6  $V_{GS}$  -  $Q_G$**



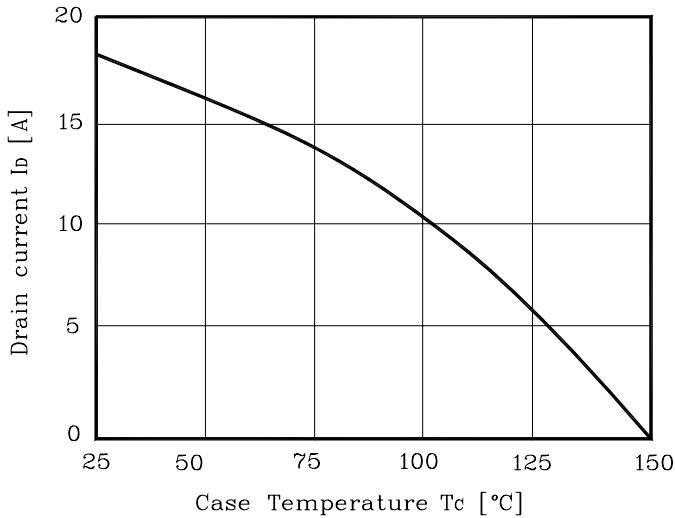
**Fig. 7  $V_{DSS}$  -  $T_J$**



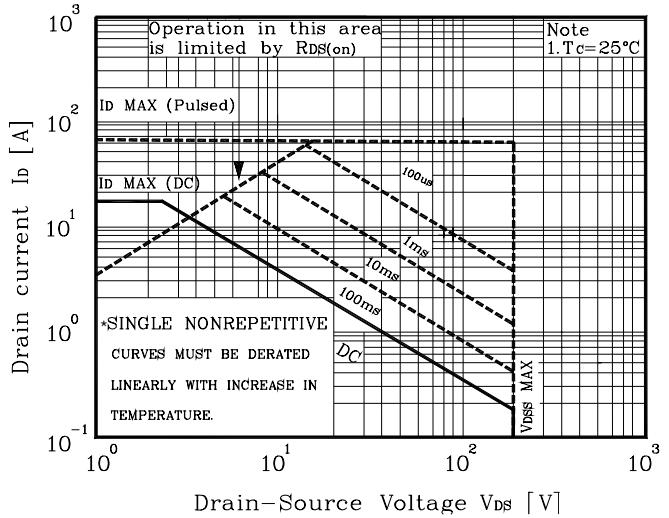
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



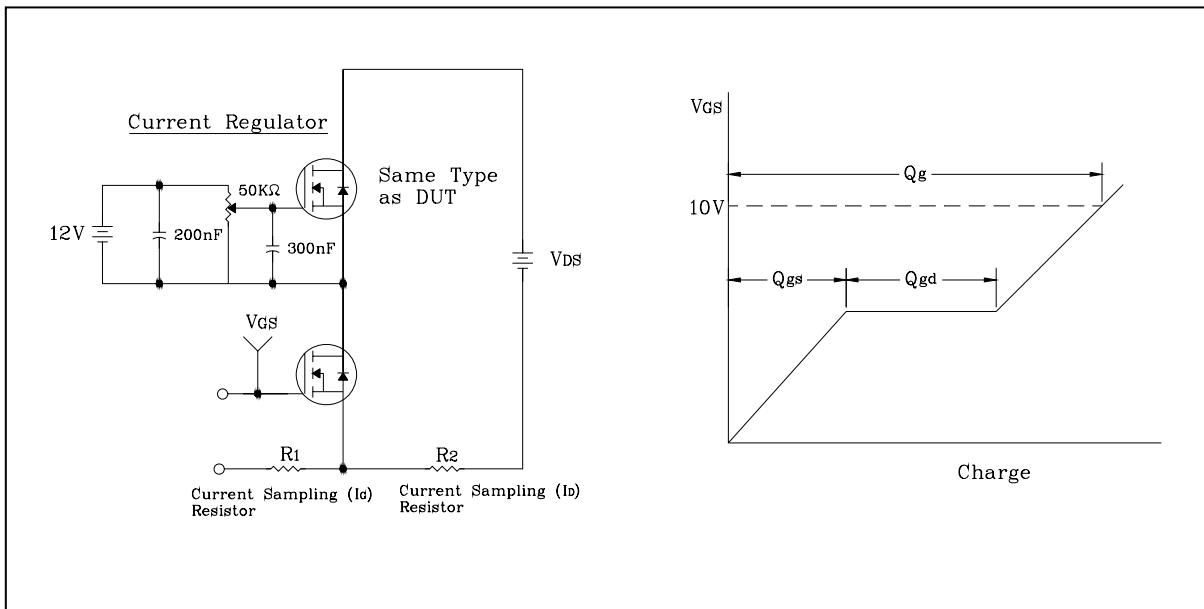
**Fig. 9  $I_D$  -  $T_C$**



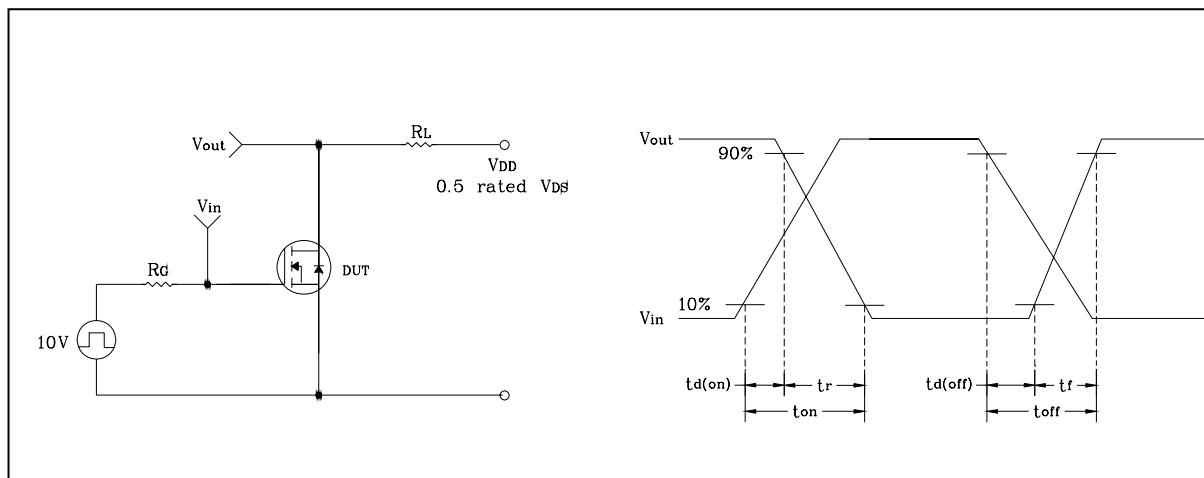
**Fig. 10 Safe Operating Area**



**Fig. 11 Gate Charge Test Circuit & Waveform**



**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

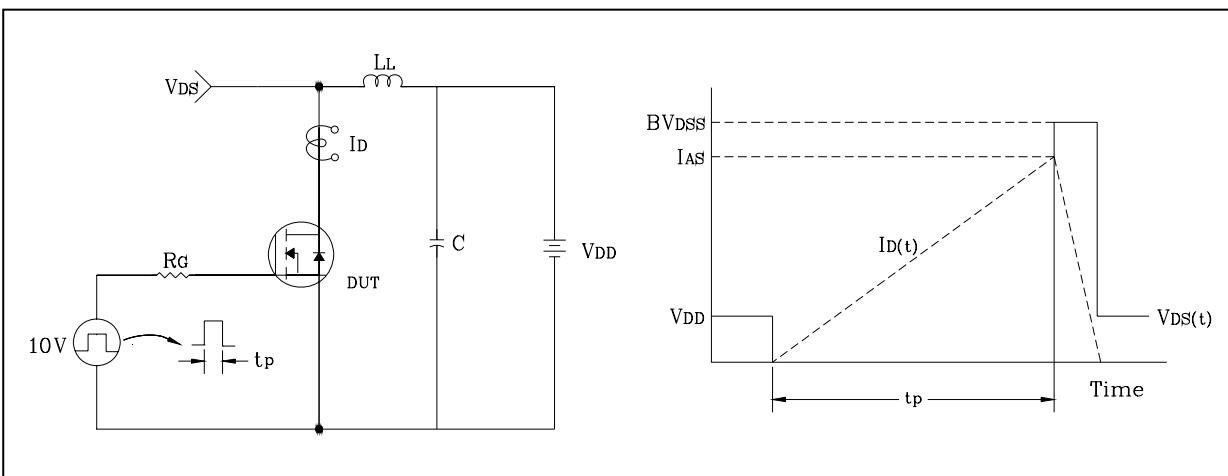
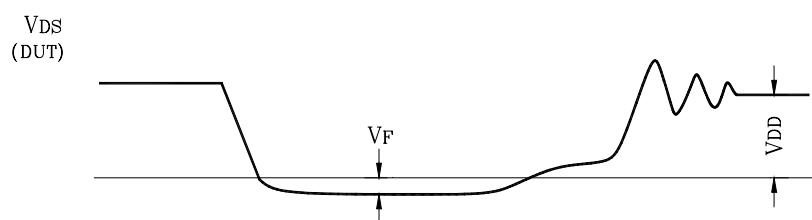
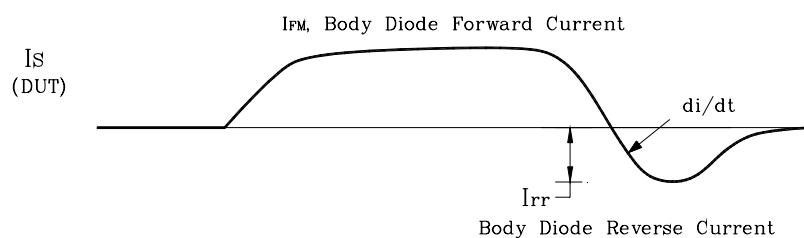
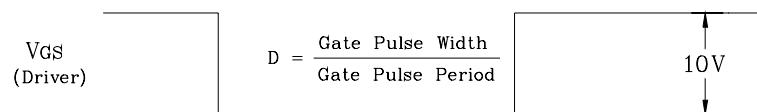
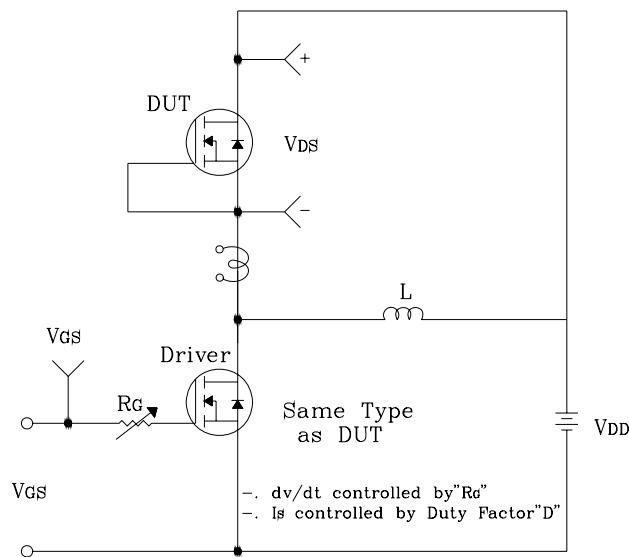
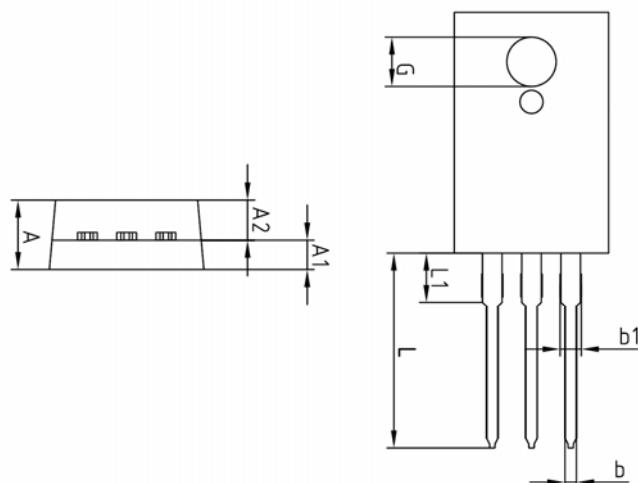
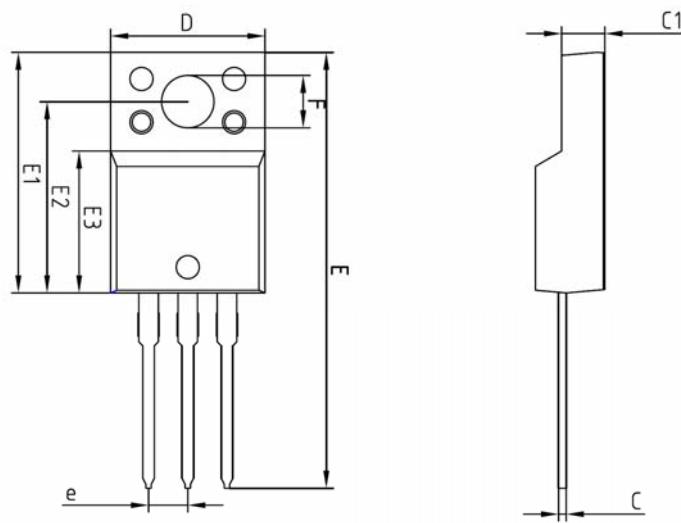


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



**Outline Dimension**

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	—	—	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	—	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	—	2.54 BSC	—	
L	12.40	—	13.00	
L1	—	3.46 BSC	—	

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